

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing Of Claims:

1-14. (Canceled)

15. (New) A method for manufacturing a component, comprising:

providing a sensor element having at least one sensitive region that is sensitive with respect to one of strain and compression;

connecting a plurality of electrical structures to the sensor element;

providing a substrate;

producing an activatable layer on top of a sacrificial layer

producing the at least one sensitive region one of on and within the activatable layer;

producing the sacrificial layer one of on and within the substrate;

producing the at least one sensitive region and at least a portion of the electrical structures one of on and within the activatable layer;

producing a circumferential trench that is interrupted by at least one connecting point connecting the at least one sensitive region of the sensor element to a portion of the activatable layer that lies outside the circumferential trench, the circumferential trench being produced around the at least one sensitive region of the sensor element;

removing the sacrificial layer below the at least one sensitive region;

fixating the at least one sensitive region by a holding device;

rupturing the at least one connecting points;

performing a transfer of the sensor element, fixated by the holding device; and

connecting the sensor element to a carrier.

16. (New) The method as recited in Claim 15, wherein the component includes a deformation sensor.

17. (New) The method as recited in Claim 15, wherein:

the sacrificial layer includes a layer of silicon oxide provided on the substrate,
the substrate includes silicon, and

the activatable layer includes one of a layer of polycrystalline silicon and a layer of monocrystalline silicon .

18. (New) The method as recited in Claim 15, further comprising:

producing the at least one sensitive region as one of a strain gauge resistor and a strain gauge strip one of on and in a region of one of a top side and a bottom side of a surface of the activatable region, the at least one sensitive region having a thickness of 1 μm to 20 μm .

19. (New) The method as recited in Claim 15, further comprising:

producing the at least one sensitive region by regional doping of the activatable layer, the regional doping including one of ion implantation and in-diffusion of foreign atoms.

20. (New) The method as recited in Claim 15, further comprising:

producing a contact region one of on and in a vicinity of the at least one sensitive region, the contact region including a superficial metal coating by which the at least one sensitive region is electrically contactable.

21. (New) The method as recited in one Claim 15, further comprising:

forming the at least one connecting point as a setpoint rupture joint; and
adjusting a mechanical stability of the at least one connecting point corresponding to the setpoint rupture joint via at least one of a thickness of the activatable layer and a form of the at least one connecting point in a plan view.

22. (New) The method as recited in Claim 15, further comprising:

producing the circumferential trench in a trench process that includes an anisotropic plasma etching process, in such a way that the circumferential trench reaches from a surface of the activatable layer down to the sacrificial layer in depth.

23. (New) The method as recited in Claim 15, further comprising:

following the production of the circumferential trench, removing the sacrificial layer below the sensor element by etching including vapor-phase etching with HF vapor in such a way that the sensor element is held above a cavity in a self-supporting manner by the at least one connecting point.

24. (New) The method as recited in Claim 15, further comprising:
producing the at least one sensitive region with a plurality of at least one of strain gauge resistors and strain gauge strips, the plurality of the at least one of strain gauge resistors and strain gauge strips being interconnected via the plurality of electrical structures to form one of a Wheatstone bridge circuit and a half-bridge of the Wheatstone bridge circuit.
25. (New) The method as recited in one Claim 15, further comprising:
producing at least a portion of the electrical structures, corresponding to one of evaluation electronics, control electronics, contact surfaces, and a bridge circuit, on one of the activatable layer and the at least one sensitive region.
26. (New) The method as recited in one Claim 15, wherein the rupturing of the at least one connecting point is implemented with the aid of a vacuum gripper that grabs the sensor element to be detached, and wherein the substrate is fixated during the rupturing by a holding device corresponding to an electrostatic clamping device.
27. (New) The method as recited in Claim 15, further comprising:
joining the sensor element to the carrier at least partially via one of a membrane region and a deformation region of the carrier, the carrier including a steel substrate.
28. (New) The method as recited in Claim 15, wherein:
a plurality of sensor elements is produced simultaneously on the substrate, and
the sensor elements are fixated by the holding device individually one after another, transferred after rupturing of the at least one connecting point, and connected to the carrier.
29. (New) The method as recited in Claim 15, wherein the ruptured sensor elements are adjusted relative to the carrier individually assigned thereto and are mounted thereon, in a continuous operation.